

Supplementary material to:

## Quantifying charge carrier concentration in ZnO thin films by Scanning Kelvin Probe Microscopy

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The Table below reports the average value as well as the standard deviation of the contact potential difference  $V_{CPD}$  measured on a set of thin film ZnO samples with different thicknesses. Each of them has been deposited under the same conditions (deposition rate 0.1 Å/sec, Ar pressure 0.8 mTorr).

Table 1. Average value and standard deviation of the  $V_{CPD}$  measured on a set of thin film ZnO samples with different thickness (from 10 to 300 nm)

Thickness (nm)	Average value and standard deviation of the $V_{CPD}$ (mV)
10	634±5
25	444±7
50	437±8
100	442±4
150	453±10
300	432±8